

ABSTRACT OF THE DISCLOSURE

STRUCTURE COMPRISING A THIN LAYER OF MATERIAL MADE UP OF CONDUCTIVE ZONES AND INSULATING ZONES AND A METHOD OF MANUFACTURING SUCH A STRUCTURE

A structure comprising a thin layer (2) that can be integral with a support (3), the thin layer being a layer of a semiconductor material made insulating by ion implantation except for at least one zone that permits a vertical electrical connection through the entire thickness of the thin layer (2). A method of manufacturing such a structure is also disclosed.

205020 65612001